

600V 0.065Ω Super Junction Power MOSFET

Description

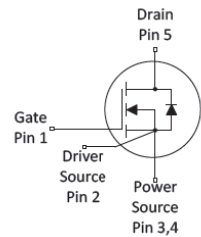
WMOS™ F2 is Wayon's 2nd generation super junction MOSFET family with fast body diode. F2 series provide all benefits of a fast switching SJ-MOSFET while offering an extremely fast body diode. WMOS™ F2 makes especially resonant switching applications more reliable.

Features

- $V_{DS} = 650V @ T_{j,max}$
- Typ. $R_{DS(on)} = 0.065\Omega$
- 100% UIS tested
- Pb-free plating, Halogen free

Applications

LED Lighting, Charger, Adapter, PC, LCD TV, Server



Absolute Maximum Ratings

Parameter	Symbol	WMZ53N60F2	Unit
Drain-source voltage	V_{DSS}	600	V
Continuous drain current ¹⁾ ($T_C = 25^\circ C$)	I_D	50	A
($T_C = 100^\circ C$)		26	A
Pulsed drain current ²⁾	I_{DM}	90	A
Gate-source voltage	V_{GS}	± 30	V
Avalanche energy, single pulse ³⁾	E_{AS}	940	mJ
Avalanche energy, repetitive ²⁾	E_{AR}	1.3	mJ
Avalanche current, repetitive ²⁾	I_{AR}	5	A
Power dissipation ($T_C = 25^\circ C$)	P_D	280	W
- Derate above $25^\circ C$		2.3	W/ $^\circ C$
Operating and storage temperature range	T_j, T_{stg}	-55 to +150	$^\circ C$
Continuous diode forward current ¹⁾	I_S	50	A
Diode pulse current ²⁾	$I_{S,pulse}$	90	A

Thermal Characteristics

Parameter	Symbol	WMZ53N60F2	Unit
Thermal resistance, junction-to-case	$R_{\theta JC}$	0.46	$^\circ C/W$
Thermal resistance, junction-to-ambient	$R_{\theta JA}$	62	$^\circ C/W$

Electrical Characteristics $T_c = 25^\circ\text{C}$, unless otherwise noted

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static characteristics						
Drain-source breakdown voltage	BV _{DSS}	V _{GS} =0 V, I _D =1 mA	600	-	-	V
Gate threshold voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =0.25mA	2	3	4.5	V
Drain cut-off current	I _{DSS}	V _{DS} =600 V, V _{GS} =0V, T _J = 25°C T _J = 125°C	- -	- 200	50 -	μA
Gate leakage current, forward	I _{GSSF}	V _{GS} =20V, V _{DS} =0V	-	-	300	nA
Gate leakage current, reverse	I _{GSSR}	V _{GS} =-20V, V _{DS} =0V	-	-	-300	nA
Drain-source on-state resistance	R _{DS(on)}	V _{GS} =10 V, I _D =8A T _J = 25°C	- -	 0.065	 0.078	 Ω
Dynamic characteristics						
Input capacitance	C _{iss}	V _{DS} = 100V, V _{GS} = 0V, f = 1 MHz	-	3400	-	pF
Output capacitance	C _{OSS}		-	115	-	
Reverse transfer capacitance	C _{rss}		-	2.7	-	
Turn-on delay time	t _{d(on)}	V _{DD} = 300V, I _D = 15A R _G = 25Ω, V _{GS} =10V	-	53	-	ns
Rise time	t _r		-	40	-	
Turn-off delay time	t _{d(off)}		-	214	-	
Fall time	t _f		-	28	-	
Gate charge characteristics						
Gate to source charge	Q _{gs}	V _{DD} =480V, I _D =15A, V _{GS} =0 to 10V	-	15.0	-	nC
Gate to drain charge	Q _{gd}		-	15.6	-	
Gate charge total	Q _g		-	58.0	-	
Gate plateau voltage	V _{plateau}		-	5.0	-	V
Reverse diode characteristics						
Diode forward voltage	V _{SD}	V _{GS} =0 V, I _F =8A	-	-	1.2	V
Reverse recovery time	t _{rr}	V _R =50V, I _F =15A, dI _F /dt=100A/μs	-	160	-	ns
Reverse recovery charge	Q _{rr}		-	2.8	-	μC
Peak reverse recovery current	I _{rrm}		-	29	-	A

Notes:

1. Limited by $T_{j\max}$. Maximum duty cycle $D=0.5$.
2. Pulse width limited by maximum junction temperature.
3. $I_{AS}=5\text{A}$, $V_{DD}=50\text{V}$, $R_G=25\Omega$, starting $T_j=25^\circ\text{C}$.

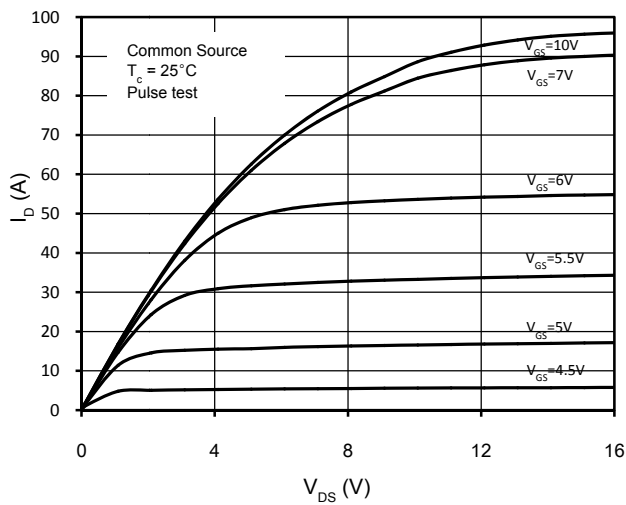


Figure 1. On-Region Characteristics

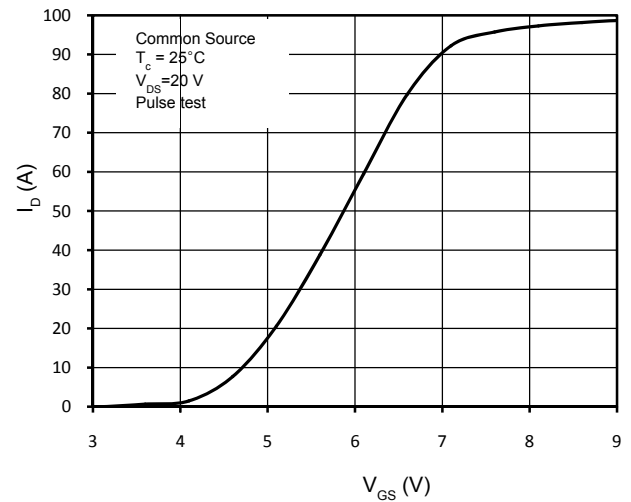


Figure 2. Transfer Characteristics

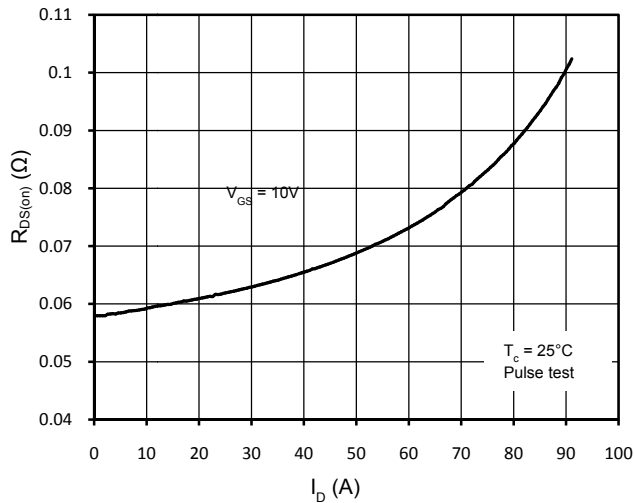


Figure 3. Static Drain-Source On Resistance

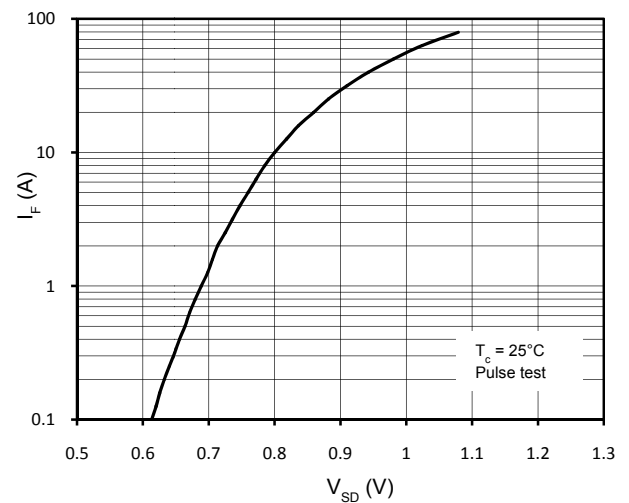
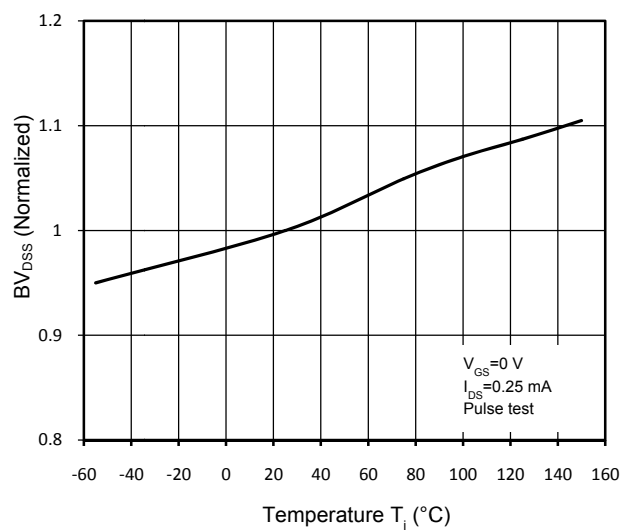
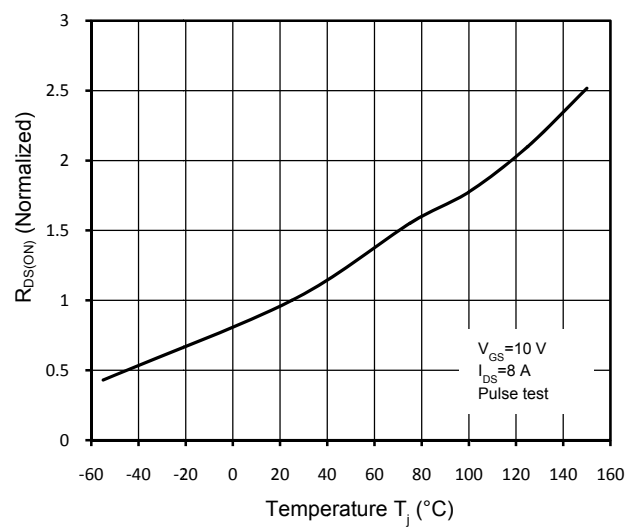


Figure 4. Body-Diode Forward Characteristics

Figure 5. Normalized BV_{DS} vs. TemperatureFigure 6. Normalized $R_{DS(on)}$ vs. Temperature

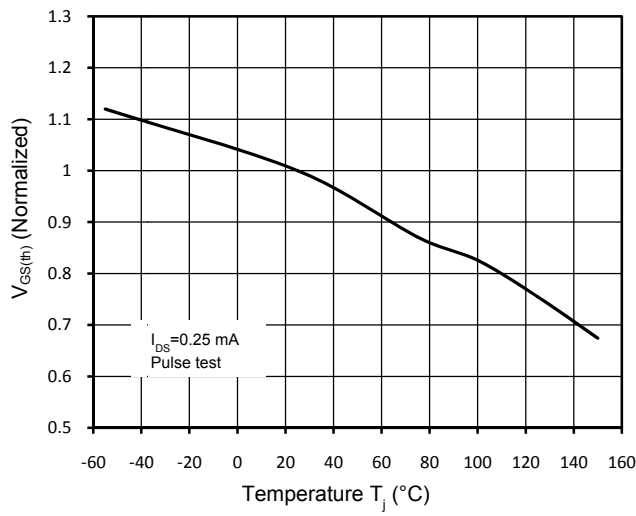


Figure 7. Threshold Voltage vs. Temperature

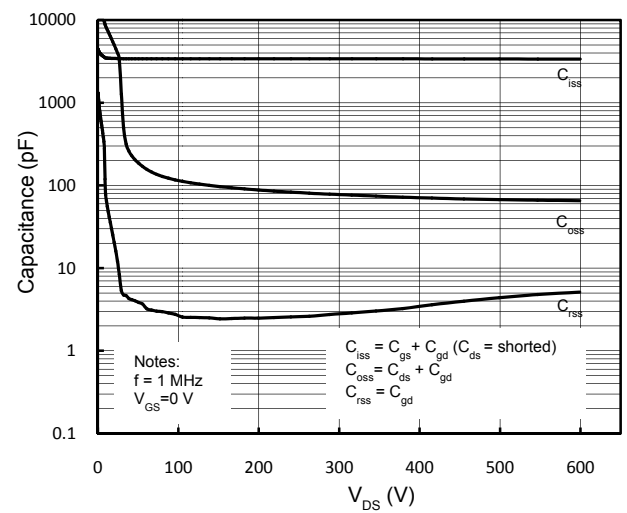


Figure 8. Capacitance Characteristics

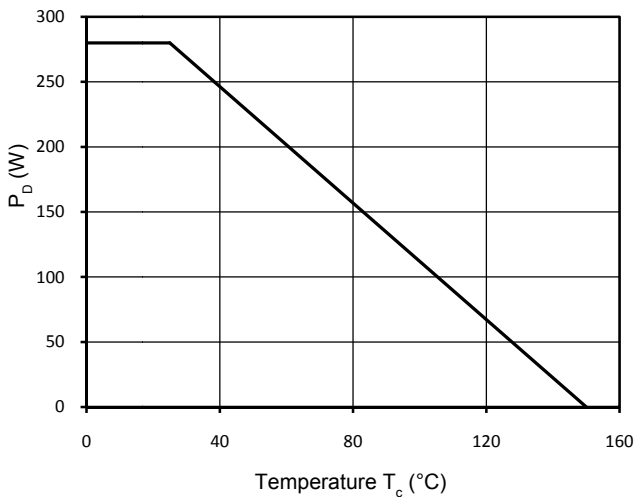


Figure 9. Power Dissipation

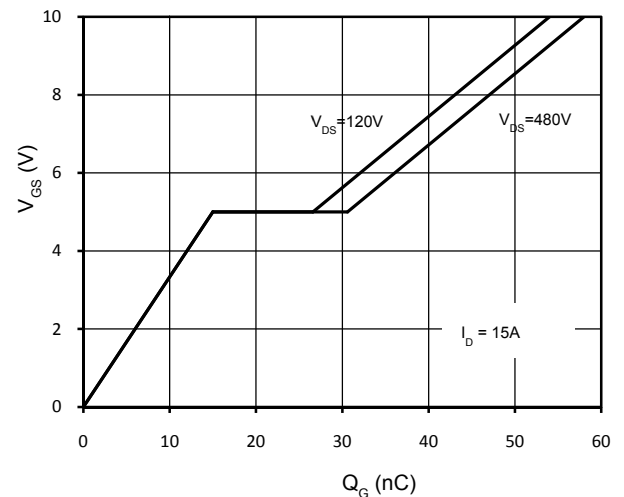


Figure 10. Gate Charge Characteristics

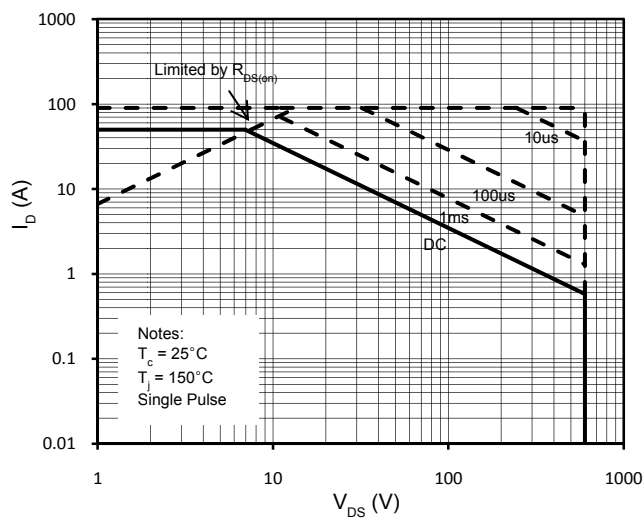


Figure 11. Maximum Safe Operating Area

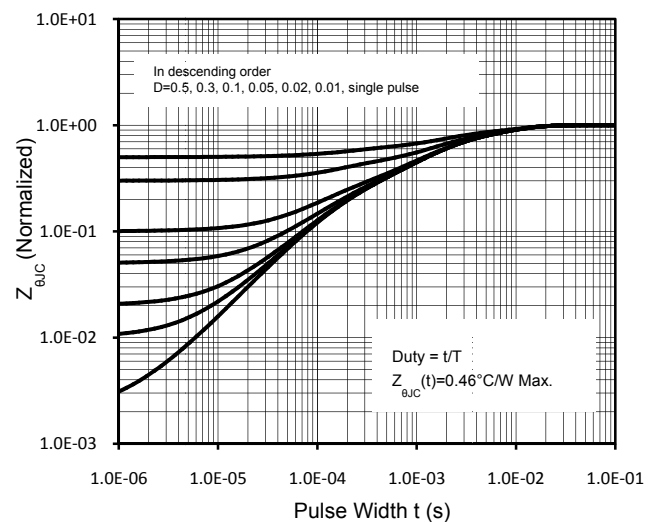
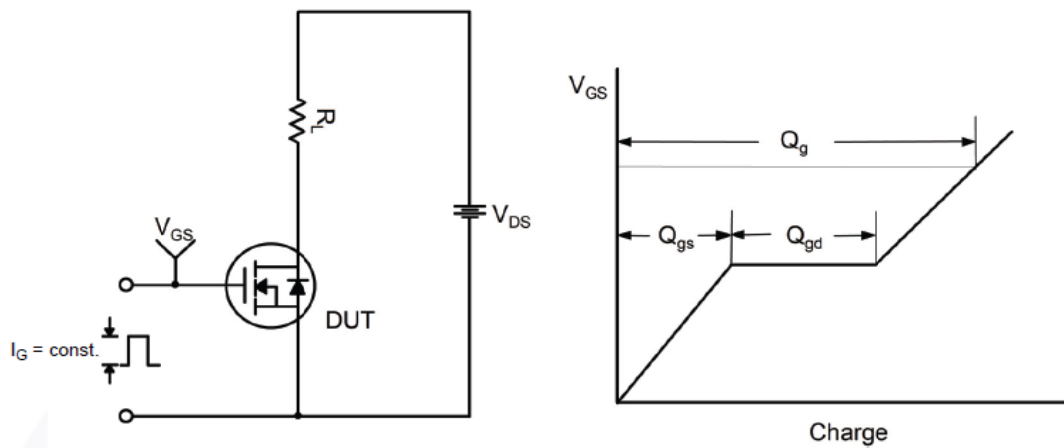
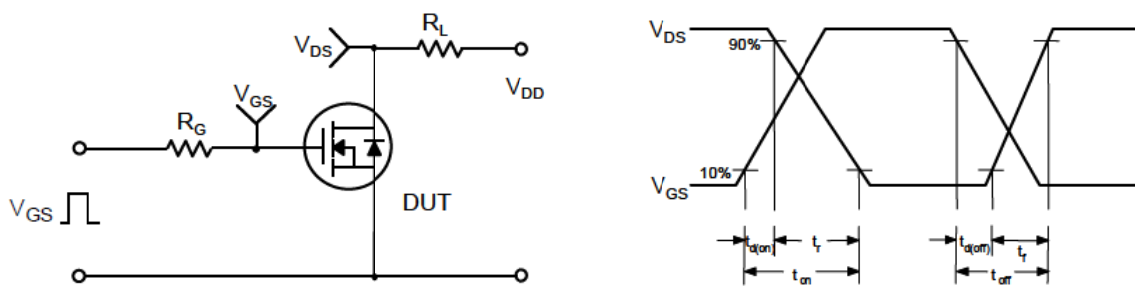


Figure 12. Transient Thermal Response Curve

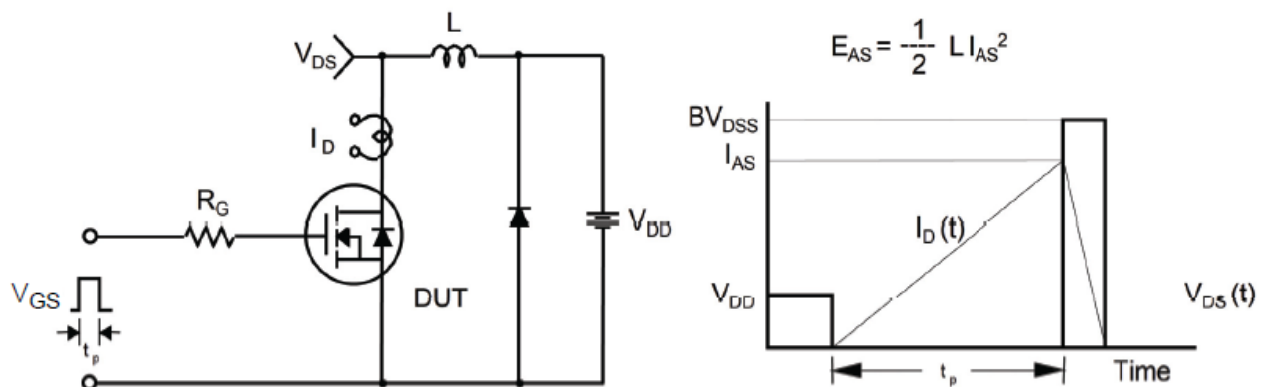
Gate Charge Test Circuit & Waveform



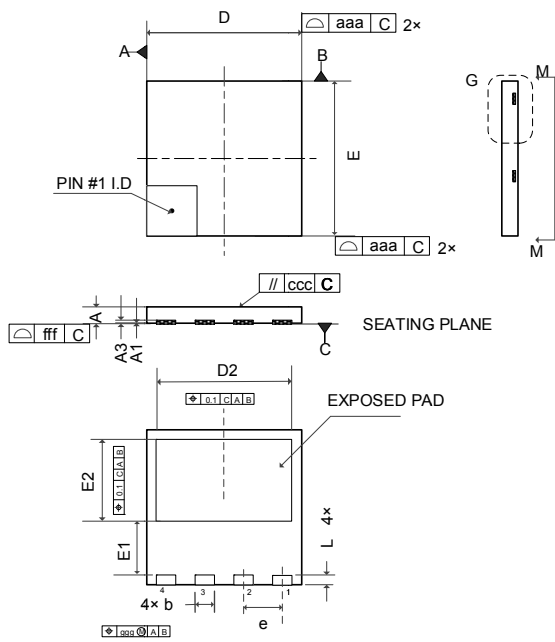
Switching Test Circuit & Waveforms



Unclamped Inductive Switching Test Circuit & Waveforms



Mechanical Dimensions for PDFN 8x8



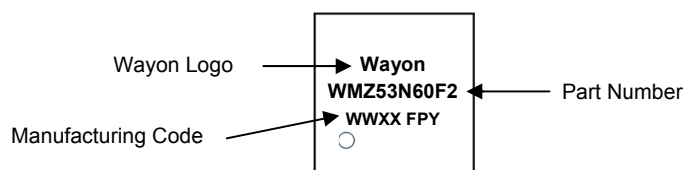
COMMON DIMENSIONS

SYMBOL	mm		
	MIN	NOM	MAX
A	0.75	0.85	0.95
A1	0.00	-	0.05
A3	0.10	0.20	0.30
b	0.90	1.00	1.10
D	7.90	8.00	8.10
E	7.90	8.00	8.10
D2	7.10	7.20	7.30
E1	2.65	2.75	2.85
E2	4.25	4.35	4.45
e	2.00 BSC		
L	0.40	0.50	0.60
aaa	0.10		
ggg	0.05		
ccc	0.05		
fff	0.05		

Ordering Information

Part	Package	Marking	Packing method
WMZ53N60F2	PDFN 8x8	WMZ53N60F2	Tape and Reel

Marking Information



Contact Information

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